



DMP3013SFV

30V P-CHANNEL ENHANCEMENT MODE MOSFET

PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
-30V	9.5mΩ @ V _{GS} = -10V	-35A
	17mΩ @ V _{GS} = -4.5V	-25A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters



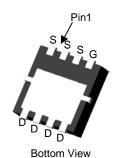
- Low R_{DS(ON)}—Ensures On-State Losses are Minimized
- Small form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

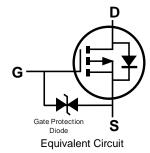
Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)



Top View





Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3013SFV-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel
DMP3013SFV-13	PowerDI3333-8 (Type UX)	3000/Tape & Reel

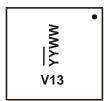
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



<u>V13</u> = Product Type Marking Code <u>YY</u>WW = Date Code Marking <u>YY</u> = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	ID	-12 -10	A
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	T _C = +25°C T _C = +70°C	ID	-35 -25	A
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	-35	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	-80	A
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	-80	А
Avalanche Current (Note 8) L = 1mH			I _{AS}	-14	А
Avalanche Energy (Note 8) L = 1mH			E _{AS}	100	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.94	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		R _{ØJA}	134	°C/W
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		PD	1.94	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		R _{ÐJA}	65	°C/W
Total Power Dissipation (Note 7)	PD	31	W	
Thermal Resistance, Junction to Case (Note 7)	R _{eJC}	4.0	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			-				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)			r			1	
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	—	—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance		_	8	9.5		V _{GS} = -10V, I _D = -11.5A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	11	17	mΩ	V _{GS} = -4.5V, I _D = -8.5A	
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1674		pF		
Output Capacitance	Coss	—	302		pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	230	—	pF	1 = 1:00012	
Gate Resistance	Rg	—	15.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg	—	16.2		nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	33.7	_	nC		
Gate-Source Charge	Q_gs	_	3.5	_	nC	V _{DS} = -15V, I _D = -11.5A	
Gate-Drain Charge	Q _{gd}	_	6.7	_	nC	7	
Turn-On Delay Time	t _{D(ON)}	_	4.0	—	ns		
Turn-On Rise Time	t _R	_	4.5	—	ns	$V_{DD} = -15V, V_{GS} = -10V,$ $R_G = 6\Omega, I_D = -11.5A$	
Turn-Off Delay Time	t _{D(OFF)}	_	96		ns		
Turn-Off Fall Time	tF		106.5		ns		
Reverse Recovery Time	t _{RR}	—	46	—	ns		
Reverse Recovery Charge	Q _{RR}	_	25.5	—	nC	$I_{\rm S} = -11.5$ A, dl/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

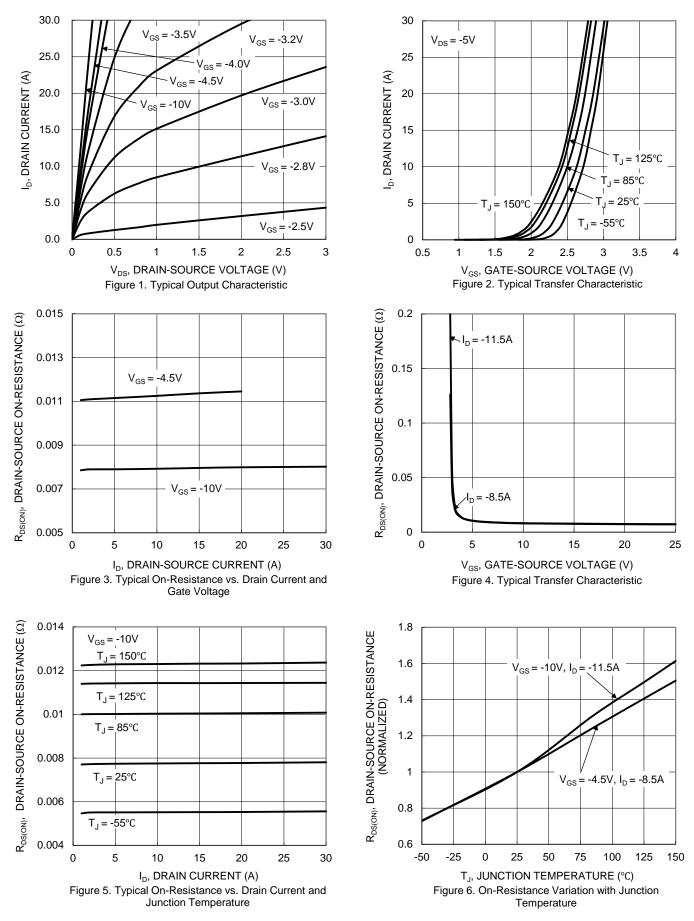
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

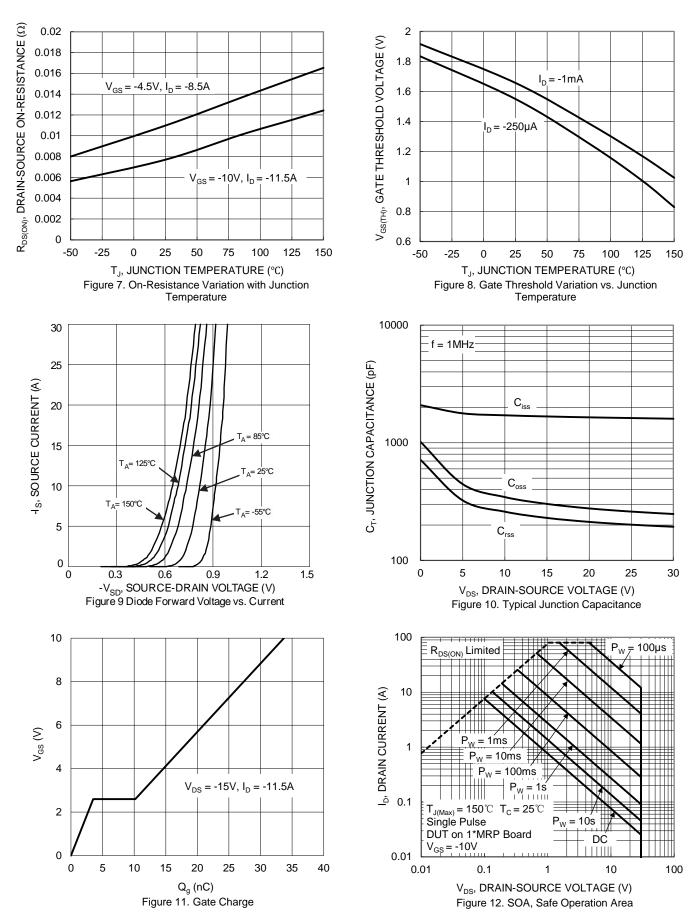




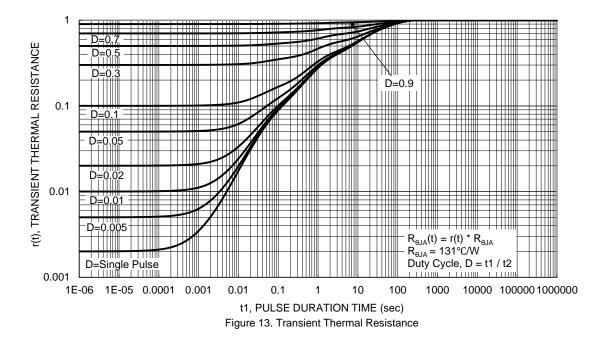
DMP3013SFV Document number: DS40141 Rev. 5 - 2



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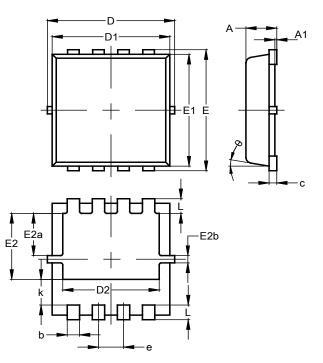






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



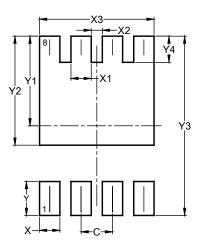
	PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E2a	0.95	1.35	1.15			
E2b	0.10	0.30	0.20			
е	0.65 BSC					
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

PowerDI3333-8 (Type UX)

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
X3	2.370			
Y	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			
Y4	0.540			



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